

PTO/SB/08A (10-01)

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Substitute for form 1449/PTO		<b>Complete if known</b>	
		Application Number	10/672,961 (Conf. No.: 9439)
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Filing Date	September 26, 2003
		First Named Inventor	Glenn J. Leedy
		Art Unit	2822
		Examiner Name	Monica Lewis
		Attorney Docket Number	ELM-2 Cont. 4
Sheet	1.	of	1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
ML		US-4,934,799	06-19-1990	Chu	

Examiner Signature		Date Considered	3/10/08
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All References Have Been Considered: \_\_\_\_\_  
Examiner\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered.  
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PTO/SB/08a/b (08-03)

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<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>				Application Number	10/672,961
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		Number-Kind Code <sup>2</sup> (if known)			
ML		US 4,604,162	08-05-1986	Sobczak	
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>2</sup> -Number <sup>2</sup> -Kind Code <sup>3</sup> (if known)				
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
ML		Jones, R.E., Jr. "An evaluation of methods for passivating silicon integrated circuits"; April 1972; pp. 23-8	
		Svechnikov, S.V.; Kobylatskaya, M.F.; Kimarskii, V.I.; Kaufman, A.P.; Kuzovlev, Yu. I.; Cherepov, Ye. I.; Pomin, B.I.; "A switching plate with aluminum membrane crossings of conductors"; 1972	
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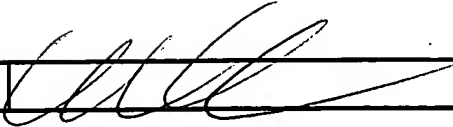
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